

# General purpose transistor (isolated transistor and diode)

## QSL12

A 2SD2675 and a RB461F are housed independently in a TSMT5 package.

**●Applications**

DC / DC converter  
Motor driver

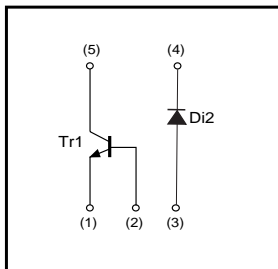
**●Features**

- 1) Tr : Low  $V_{CE(sat)}$   
Di : Low  $V_f$
- 2) Small package

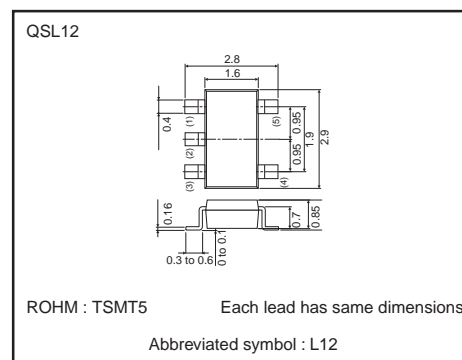
**●Structure**

Silicon epitaxial planar transistor  
Schottky barrier diode

**●Equivalent circuit**



**●External dimensions (Unit : mm)**



**●Packaging specifications**

Type	QSL12
Package	TSMT5
Marking	L12
Code	TR
Basic ordering unit(pieces)	3000

Transistors

●Absolute maximum ratings (Ta=25°C)

Tr1

Parameter	Symbol	Limits	Unit
Collector-base voltage	V <sub>CB0</sub>	30	V
Collector-emitter voltage	V <sub>CEO</sub>	30	V
Emitter-base voltage	V <sub>EBO</sub>	6	V
Collector current	I <sub>c</sub>	1	A
	I <sub>CP</sub>	2	A *1
Power dissipation	P <sub>c</sub>	0.9	W / ELEMENT *2
Junction temperature	T <sub>j</sub>	150	°C
Range of storage temperature	T <sub>stg</sub>	-40 to +125	°C

\*1 Single pulse, Pw=1ms

\*2 Mounted on a 25mm×25mm×0.8mm ceramic substrate

Di2

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V <sub>RM</sub>	25	V
Reverse voltage (DC)	V <sub>R</sub>	20	V
Average rectified forward current	I <sub>F</sub>	700	mA
Forward current surge peak (60Hz, 1∞)	I <sub>FSM</sub>	3	A
Power dissipation	P <sub>D</sub>	0.7	W / ELEMENT *
Junction temperature	T <sub>j</sub>	125	°C
Range of storage temperature	T <sub>stg</sub>	-40 to +125	°C

\* Mounted on a 25mm×25mm×0.8mm ceramic substrate

Tr1&Di2

Parameter	Symbol	Limits	Unit
Total power disipation	P <sub>D</sub>	0.5	W / TOTAL *1
		1.25	W / TOTAL *2

\*1 Each terminal mounted on a recommended land.

\*2 Mounted on a 25mm×25mm×0.8mm ceramic substrate.

●Electrical characteristics (Ta=25°C)

Tr1

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV <sub>CB0</sub>	30	-	-	V	I <sub>c</sub> =10μA
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	30	-	-	V	I <sub>c</sub> =1mA
Emitter-base breakdown voltage	BV <sub>EBO</sub>	6	-	-	V	I <sub>E</sub> =10μA
Collector cutoff current	I <sub>cBO</sub>	-	-	100	nA	V <sub>CB</sub> =30V
Emitter cutoff current	I <sub>EBO</sub>	-	-	100	nA	V <sub>EB</sub> =6V
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	-	120	350	mV	I <sub>c</sub> /I <sub>B</sub> =500mA/25mA
DC current gain	h <sub>FE</sub>	270	-	680	-	V <sub>CE</sub> /I <sub>c</sub> =2V/100mA *
Transition frequency	f <sub>r</sub>	-	320	-	MHz	V <sub>CE</sub> =2V, I <sub>E</sub> =-100mA, f=100MHz *
Collector output capacitance	C <sub>ob</sub>	-	7	-	pF	V <sub>CB</sub> =10V, I <sub>E</sub> =0A, f=1MHz

\* Pulsed

Di2

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V <sub>F</sub>	-	450	490	mV	I <sub>F</sub> =700mA
Reverse current	I <sub>R</sub>	-	-	200	μA	V <sub>R</sub> =20V
Reverse recovery time	t <sub>rr</sub>	-	9	-	ns	I <sub>F</sub> =I <sub>R</sub> =100mA, I <sub>rr</sub> =0.1I <sub>R</sub>

Transistors

●Electrical characteristic curves

Tr1

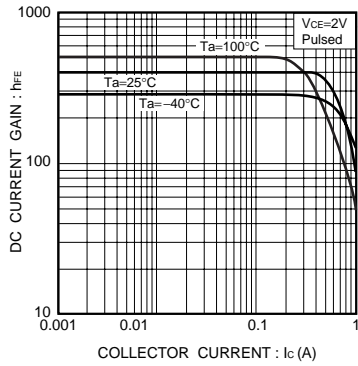


Fig.1 DC current gain vs. collector current

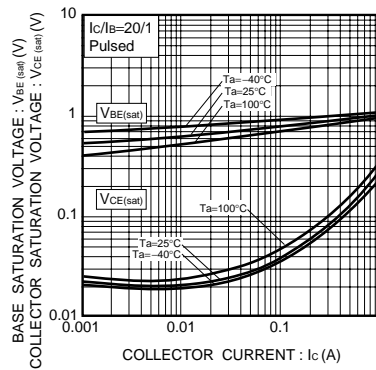


Fig.2 Collector-emitter saturation voltage vs. collector current

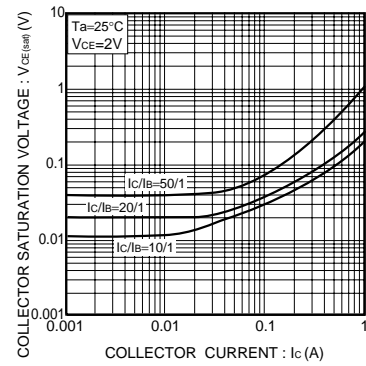


Fig.3 Collector-emitter saturation voltage vs. collector current

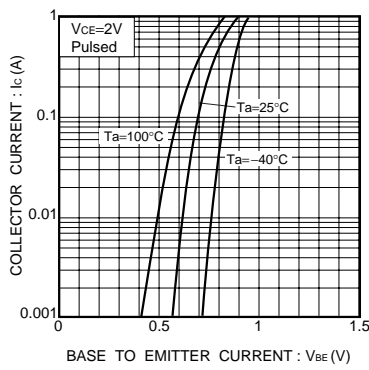


Fig.4 Grounded emitter propagation characteristics

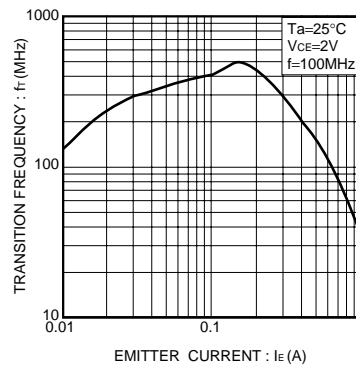


Fig.5 Gain bandwidth product vs. emitter current

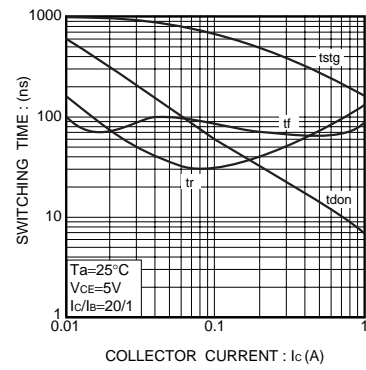


Fig.6 Switching time

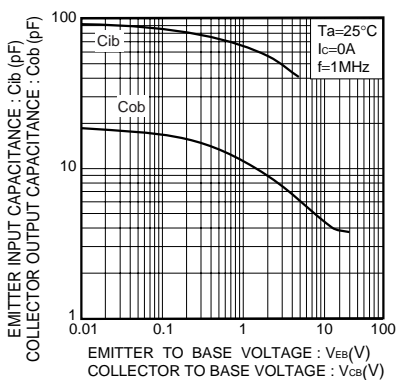


Fig.7 Collector output capacitance vs. collector-base voltage  
Emitter input capacitance vs. emitter-base voltage

Transistors

Di2

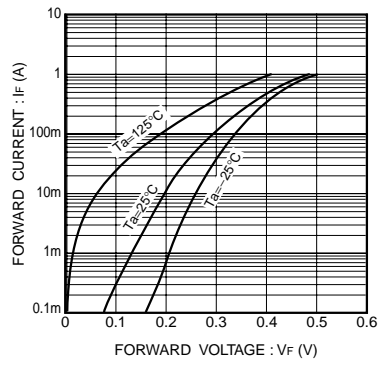


Fig.8 Forward characteristics

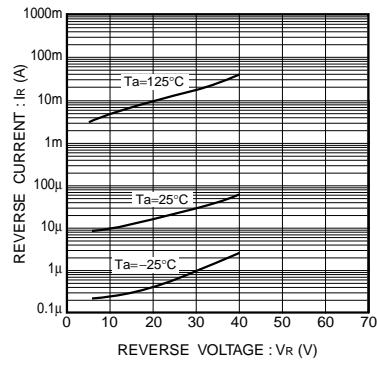


Fig.9 Reverse characteristics

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